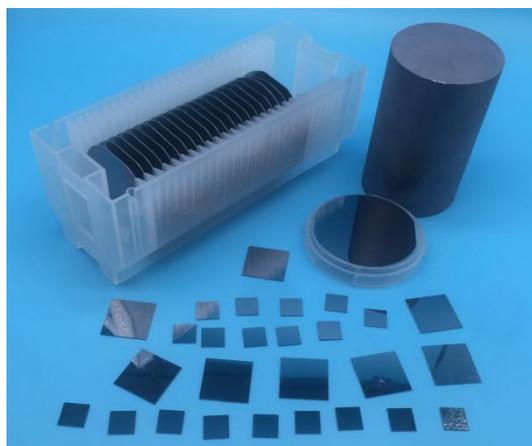


Gallium Arsenide(GaAs)

Gallium arsenide (GaAs) is a compound synthesized by two elements of gallium and arsenic. It is an important group IIIA and group VA compound semiconductor material. And it can be used to make microwave integrated circuits, infrared light-emitting diodes, semiconductor lasers and solar cells. GaAs is often used as the base material for the epitaxial growth of III-V semiconductors, including indium gallium arsenide, aluminum gallium arsenide, and so on.



PARAMETERS

Single Crystal	Doping	Conductivity Type	Carrier Concentration (cm ⁻³)	Dislocation Density (cm ⁻²)	Growth Method	Standard Substrate
GaAs	None	Si	/	<5×10 ⁵	LEC HB Dia3"	Dia3"×0.5 Dia2"×0.5
	Si	N	>5×10 ¹⁷			
	Cr	Si	/			
	Fe	N	~2×10 ¹⁸			
	Zn	P	>5×10 ¹⁷			
Dimension		25×25×0.5mm、10×10×0.5mm、10×5×0.5mm、5×5×0.5mm According to customer needs, substrates with special orientation and size can be customized.				
Surface Roughness		Surface roughness(Ra):<=5Å Atomic Particle Microscopy (AFM) test report can be provided.				
Polishing		One side or two sides				
Package		Class 100 clean bag, Class 1000 super clean room				